Data Sheet

Central™
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Manufacturers of World Class Discrete Semiconductors

1N914A
1N914B

SILICON SWITCHING DIODE

JEDEC DO-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N914A,B types are very high speed Silicon Switching Diodes designed for computer and general purpose applications.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNIT
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Peak Working Reverse Voltage	V_{RWM}	75	V
Average Forward Current	I_O	150	mA
Forward Steady-State Current	I_F	200	mA
Peak Forward Surge Current(1.0μs pulse)	I_{FSM}	2000	mA
Power Dissipation	P_D	500	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 TO +200	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

		1N914A		1N914B		
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	UNIT
BV_R	I_R=5.0μA	75		75		V
BV_R	I_R=100μA	100		100		V
I_R	V_R=20V		25		25	nA
I_R	V_R=20V, T_A=100°C		-		3.0	μA
I_R	V_R=20V, T_A=150°C		50		50	μA
V_F	I_F=5.0mA	-	-	0.62	0.72	V
V_F	I_F=20mA		1.0		-	V
V_F	I_F=100mA		-		1.0	V
C_T	V_R=0, f=1.0 MHz		4.0		4.0	pF
t_{rr}	V_R=6.0V, I_F=10mA I_{rr}=1.0mA, R_L=100Ω		4.0		4.0	nS
$V_{FM(REC)}$	I_F=50mA, R_l=50Ω		-		2.5	V